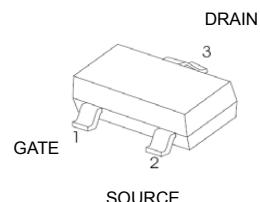
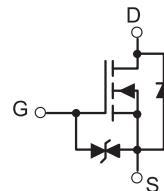




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## BSS123KT N Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	$I_D$
100V	6Ω@10V	0.17A
	10Ω@4.5V	



**SOT-523**

### FEATURE

- Surface Mount Package
- High Density Cell Design for Extremely Low  $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable
- ESD protected

### APPLICATION

- Small Servo Motor Controls
- Power MOSFET Gate Drivers
- Switching Application

MARKING : 123

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
<b>N-MOSFET</b>			
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current (note 1)	$I_D$	0.17	A
Pulsed Drain Current ( $t_p=10\mu\text{s}$ )	$I_{DM}$	0.68	A
Continuous Source-Drain Diode Current	$I_S$	0.17	A
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	357	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	$T_L$	260	°C



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## MOSFET ELECTRICAL CHARACTERISTICS

T<sub>a</sub>=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>STATIC CHARACTERISTICS</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	100			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> = 0V			1	μA
		V <sub>DS</sub> =20V,V <sub>GS</sub> = 0V			100	nA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±2	uA
Gate threshold voltage (note 2)	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1		2.5	V
Drain-source on-resistance(note 2)	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.17A			10	Ω
		V <sub>GS</sub> =10V, I <sub>D</sub> =0.17A			6	Ω
Forward tranconductance(note 2)	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =170mA	80			mS
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =340mA, V <sub>GS</sub> = 0V			1.3	V
<b>DYNAMIC CHARACTERISTICS (note 4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,f =1MHz		29	60	pF
Output Capacitance	C <sub>oss</sub>			10	15	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			2	6	pF
<b>SWITCHING CHARACTERISTICS (note 3,4)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V,V <sub>DD</sub> =30V, I <sub>D</sub> =2.8A,R <sub>GEN</sub> =50 Ω			8	ns
Turn-on rise time	t <sub>r</sub>				8	ns
Turn-off delay time	t <sub>d(off)</sub>				13	ns
Turn-off fall time	t <sub>f</sub>				16	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =0.22A, V <sub>GS</sub> =10V		1.4	2	nC
Gate-Source Charge	Q <sub>gs</sub>			0.15	0.25	nC
Gate-Drain Charge	Q <sub>gd</sub>			0.2	0.4	nC

### Notes :

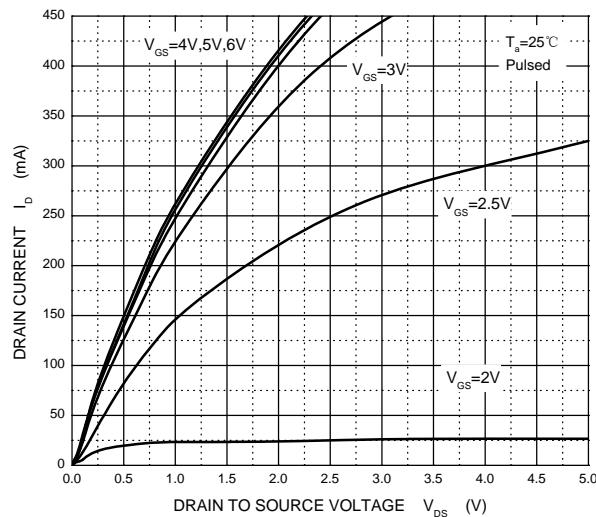
- 1.Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse width=300μs, duty cycle≤2%.
3. Switching characteristics are independent of operating junction temperature.
4. Garanteed by design, not subject to producing.



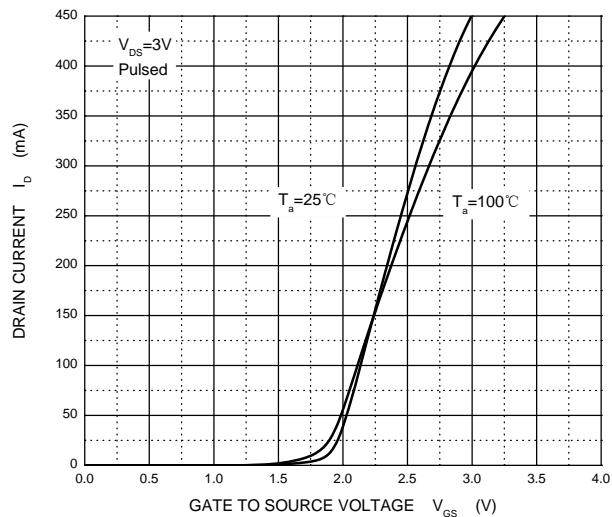
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## Typical Characteristics

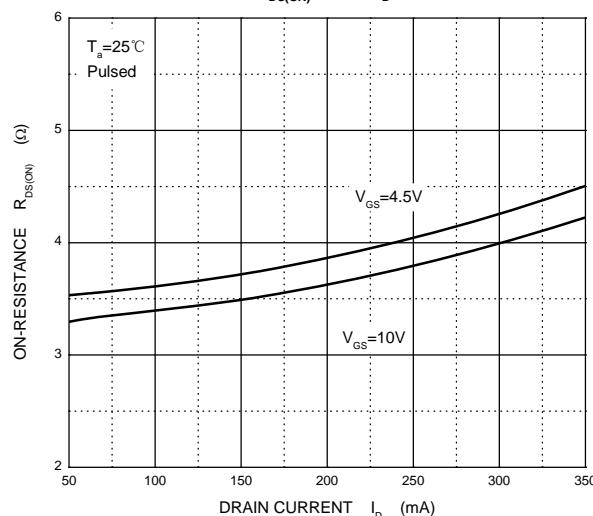
Output Characteristics



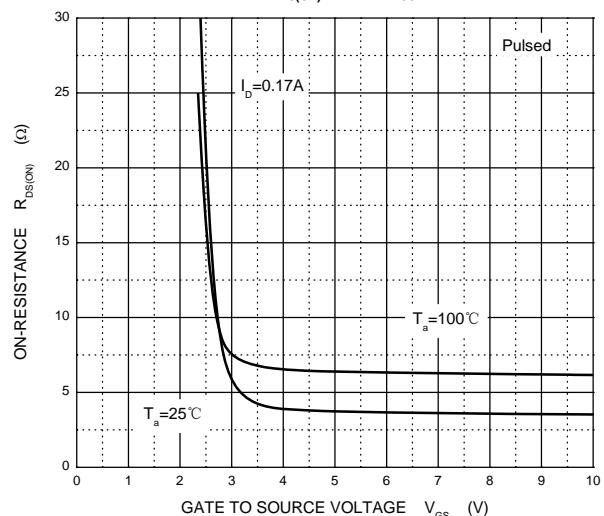
Transfer Characteristics



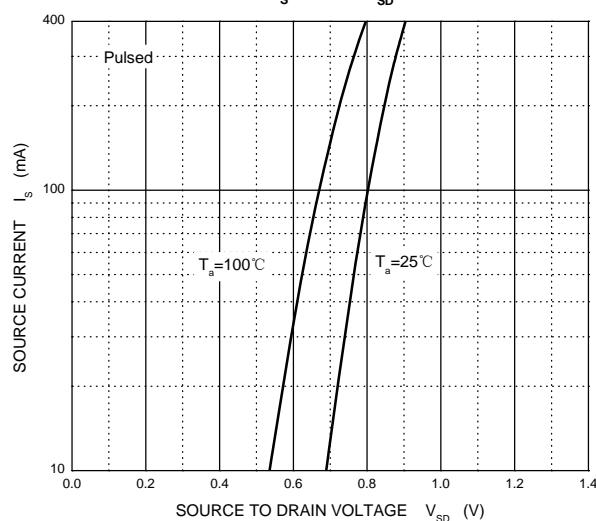
$R_{DS(ON)}$  —  $I_D$



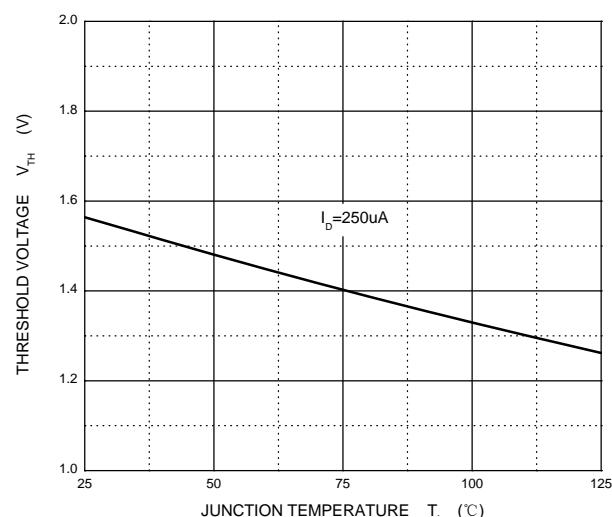
$R_{DS(ON)}$  —  $V_{GS}$



$I_S$  —  $V_{SD}$



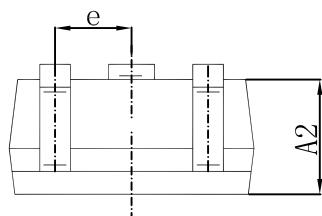
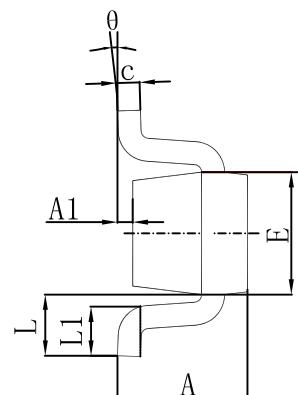
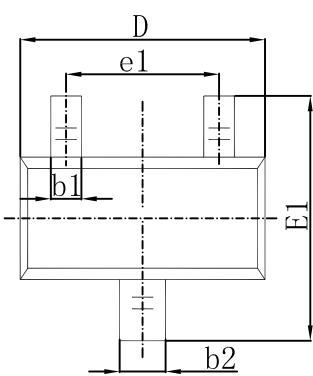
Threshold Voltage





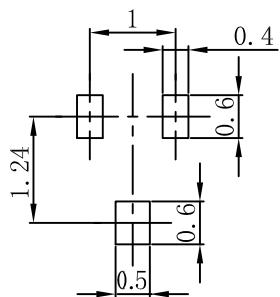
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### SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

### SOT-523 Suggested Pad Layout



#### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.